



10013802-1

Response

In re Patent Application of:

Inventor:

Chen, et al

Confirmation No:

1660

Serial No.

10/085,866

Examiner:

Hu, Shouxiang

Filed:

Feb 27, 2002

Group Art Unit:

2811

Title:

Emission Layer Formed By Rapid Thermal Formation Process

Commissioner for Patents P O BOX 1450 Alexandria VA 22313-1450

RESPONSE TO RESTRICTION REQUIREMENT

In response to your Office Action/Restriction Requirement dated July 1, 2003; Applicants affirm the election of **Group II**, (Claims 13-19) without traverse.

Hewlett-Packard Company 1000 NE Circle Blvd. m/s 422B Corvallis, OR 97330 (541) 715-4197

Respectfully submitted.

Chen, et al

Timothy F. Myers,

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Attorney For Applicants

I hereby certify that this correspondence is being deposited on the date indicated below with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, PQ-Box 1450, Alexandria, VA 22313.

Signature

Typed Name

Date of Signature

10013802

PATENT

<u>IN</u>	THE UNITED STATES PATENT A	ND TRADEMARK OFFIC	E #4 Per Andt
In Re U.S. Pa	atent Application MAR 2 9 2002 8)	E #4 Per Andt - 5-21-02 Retulu
Applicant:	Chen et al.)	1
Serial No.:	10/085866)	
Filing Date:	Feb 27 2002))	TEC
For:	EMISSION LAYER FORMED BY RAPID THERMAL FORMATION PROCESS)))	RECEIVED APR -4 2002 FECHNOLOGY CENTER 2800
Art Unit:	Unassigned)	ENTER
PRELIMINARY AMENDMENT			

Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir:

Prior to consideration and calculating the fees for the above-referenced Application, please amend the Application as follows:

In the Specification:

Please replace the paragraph beginning on page 3, line $\frac{30}{20}$, with the following rewritten paragraph:

Referring now to FIG. 1, a preferred embodiment emitter 10 of the invention is shown in a two-dimensional schematic cross section. The preferred embodiment emitter 10 is a metal-insulator-semiconductor (MIS) device including a flat